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### 30 V, 200 mA dual P-channel Trench MOSFET

Rev. 1 — 1 August 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### **1.2 Features and benefits**

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology

#### **1.3 Applications**

- Relay driver
- High-speed line driver

- ESD protection up to 2 kV
- AEC-Q101 qualified
- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Mir	і Тур	Max	Unit
Per transist	or					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C	-	-	-30	V
V <sub>GS</sub>	gate-source voltage		-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	<u>[1]</u> _	-	-200	mA
Static chara	cteristics (per transistor)					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -200 mA; T <sub>i</sub> = 25 °C	-	2.8	4.1	Ω

 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



30 V, 200 mA dual P-channel Trench MOSFET

### 2. Pinning information

Table 2.	Pinning	g information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		24 - 22
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		$G1 \left( \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$
5	G2	gate TR2		
6	D1	drain TR1	SOT363 (SC-88)	
				S1 S2 017aaa260

### 3. Ordering information

Table 3. Orde	ering information		
Type number	Package		
	Name	Description	Version
NX3008PBKS	SC-88	plastic surface-mounted package; 6 leads	SOT363

### 4. Marking

Table 4.	Marking	codes
----------	---------	-------

Type number	Marking code <sup>[1]</sup>
NX3008PBKS	LC%

[1] % = placeholder for manufacturing site code.

30 V, 200 mA dual P-channel Trench MOSFET

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C	-	-30	V
V <sub>GS</sub>	gate-source voltage		-8	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$	<u>[1]</u> _	-200	mA
		$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u> -	-125	mA
I <sub>DM</sub>	peak drain current	$T_{amb} = 25 \text{ °C}$ ; single pulse; $t_p \le 10 \mu\text{s}$	-	-0.8	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2] _	280	mW
			<u>[1]</u> _	320	mW
		T <sub>sp</sub> = 25 °C	-	990	mW
Per device	•				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2] _	445	mW
Tj	junction temperature		-55	150	°C
T <sub>amb</sub>	ambient temperature		-55	150	°C
T <sub>stg</sub>	storage temperature		-65	150	°C
Source-dra	ain diode				
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u> _	-200	mA
ESD maxir	num rating				
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	2000	V

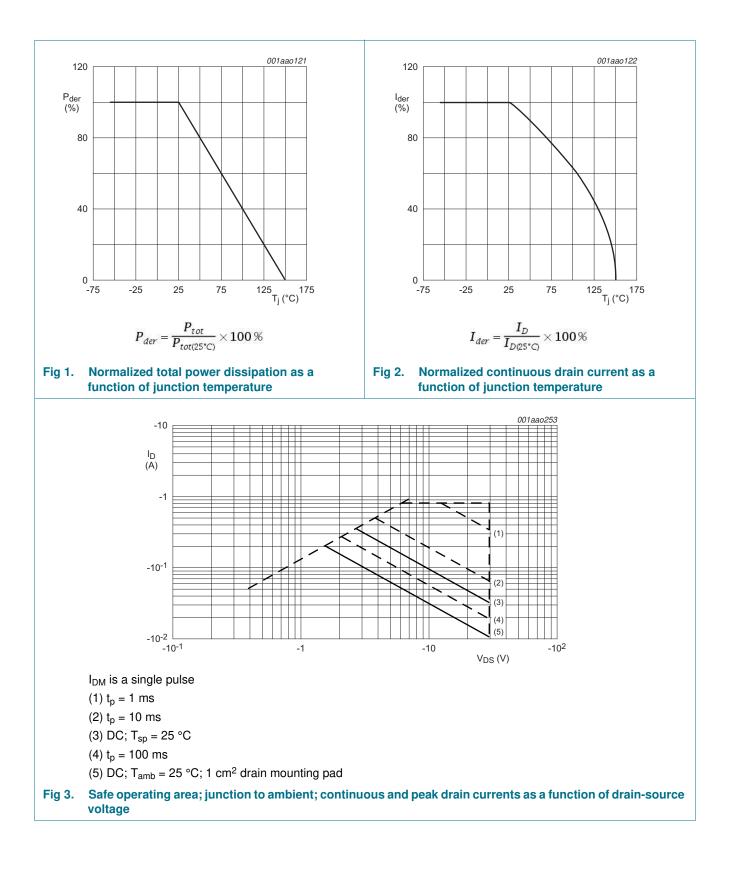
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

# NX3008PBKS

#### 30 V, 200 mA dual P-channel Trench MOSFET



NX3008PBKS Product data sheet

30 V, 200 mA dual P-channel Trench MOSFET

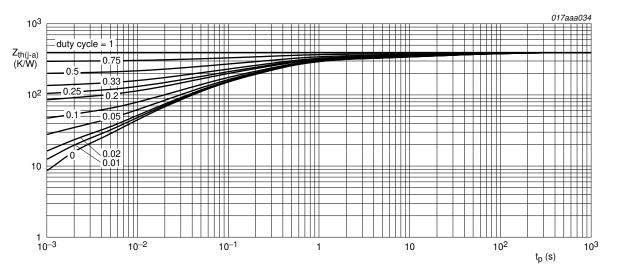
### 6. Thermal characteristics

Table 6.	I nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per devic	e					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W
Per trans	istor					
R <sub>th(j-a)</sub>	thermal resistance from junction to	in free air	[1] -	390	445	K/W
	ambient		[2] _	340	390	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	130	K/W

#### Table 6.Thermal characteristics

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

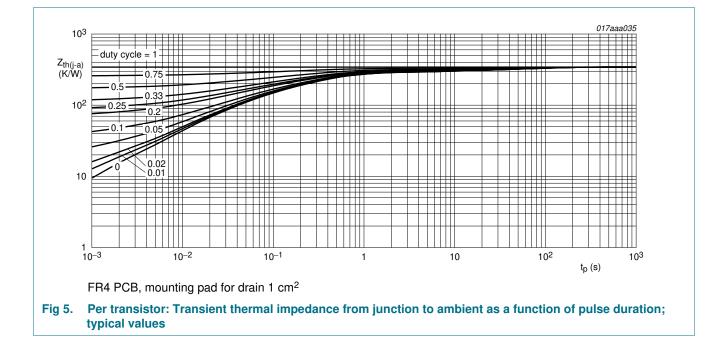


FR4 PCB, standard footprint

Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# NX3008PBKS

#### 30 V, 200 mA dual P-channel Trench MOSFET



Product data sheet

30 V, 200 mA dual P-channel Trench MOSFET

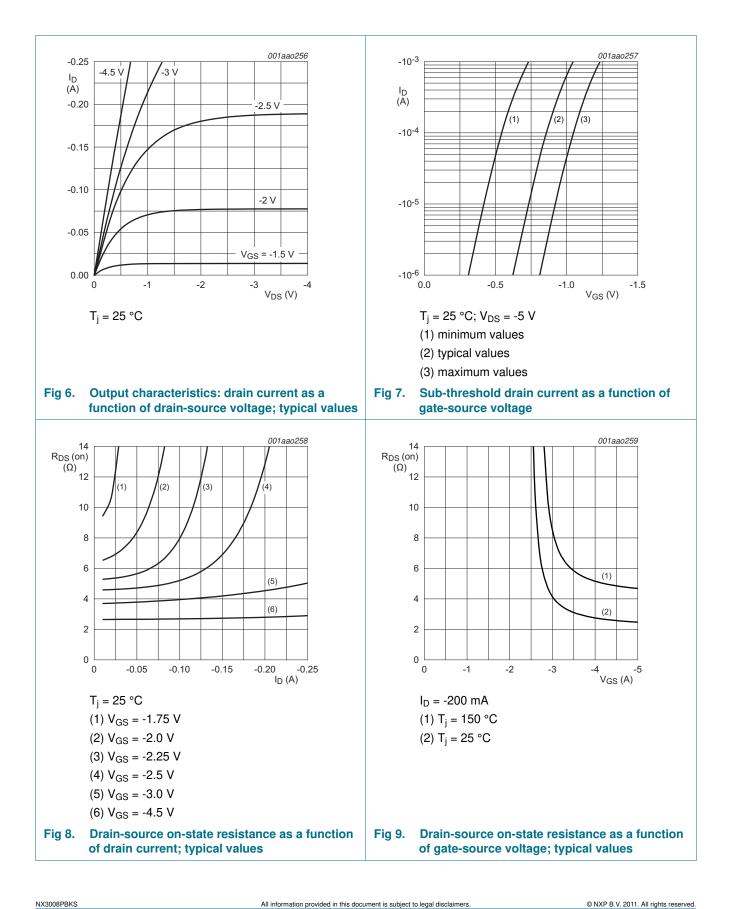
### 7. Characteristics

Table 7.	Characteristics	<b>A</b> 1111		-		
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
	racteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = -250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^\circ\text{C}$	-0.6	-0.9	-1.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
		$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 °C$	-	-0.2	-1	μA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.2	-1	μA
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-10	-	nA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-10	-	nA
		$V_{GS}$ = 2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-1	-	nA
		$V_{GS}$ = -2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-1	-	nA
DOUL	drain-source on-state	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -200 mA; T <sub>j</sub> = 25 °C	-	2.8	4.1	Ω
	resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -200 mA; T <sub>j</sub> = 150 °C	-	5.3	7.8	Ω
		$V_{GS}$ = -2.5 V; I <sub>D</sub> = -10 mA; T <sub>j</sub> = 25 °C	-	5.3	6.5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -200 mA; $T_{j}$ = 25 °C	-	160	-	mS
Dynamic o	haracteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -15 \text{ V}; I_D = -200 \text{ mA};$	-	0.55	0.72	nC
Q <sub>GS</sub>	gate-source charge	V <sub>GS</sub> = -4.5 V; T <sub>j</sub> = 25 °C	-	0.23	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.09	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -15 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	31	46	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}$	-	6.5	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	2.3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -20 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = -4.5 V;	-	19	38	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	65	130	ns
t <sub>f</sub>	fall time		-	38	-	ns
Source-dra	ain diode (per transistor)					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -200 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-0.47	-0.88	-1.2	V

NX3008PBKS Product data sheet

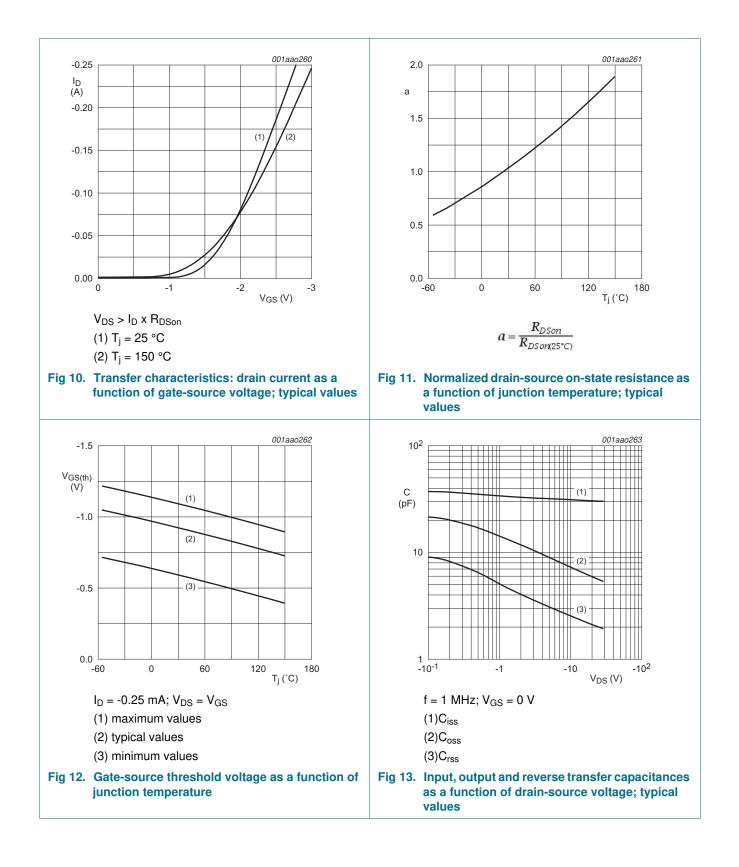
# NX3008PBKS

#### 30 V, 200 mA dual P-channel Trench MOSFET



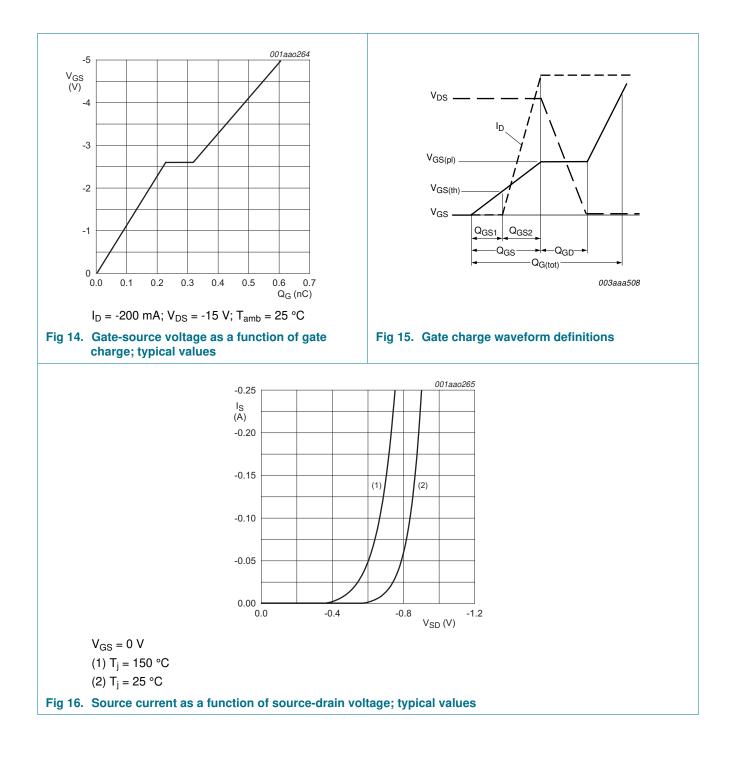
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#### 30 V, 200 mA dual P-channel Trench MOSFET



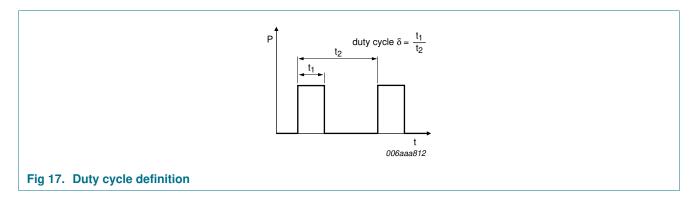
# NX3008PBKS

#### 30 V, 200 mA dual P-channel Trench MOSFET



30 V, 200 mA dual P-channel Trench MOSFET

### 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

NX3008PBKS Product data sheet

30 V, 200 mA dual P-channel Trench MOSFET

### 9. Package outline

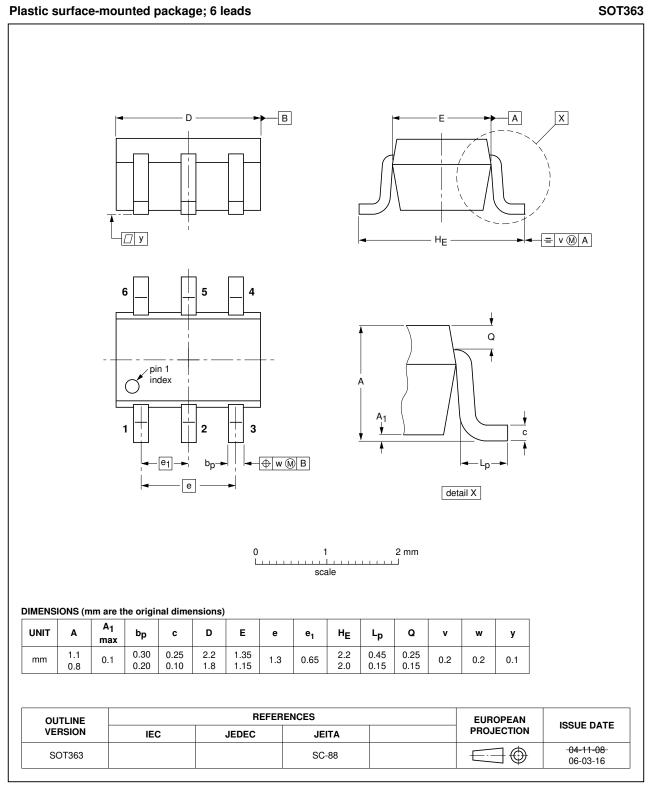


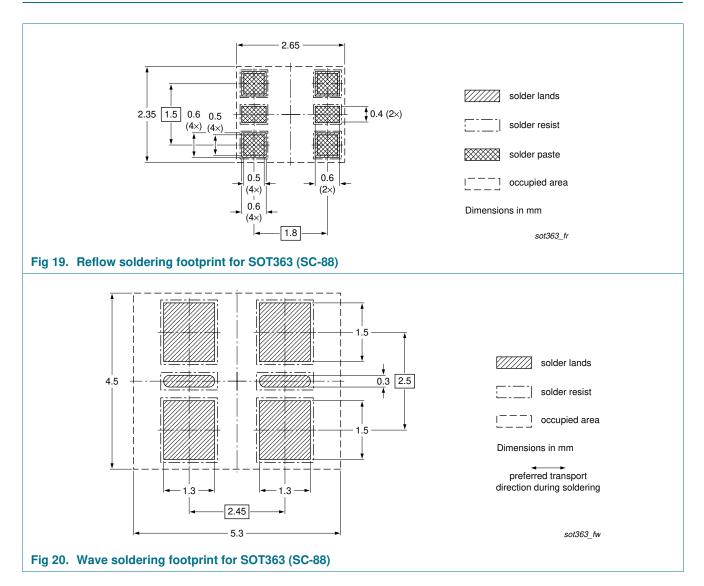
Fig 18. Package outline SOT363 (SC-88)

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30 V, 200 mA dual P-channel Trench MOSFET

### **10. Soldering**



30 V, 200 mA dual P-channel Trench MOSFET

### **11. Revision history**

Table 8. Revis	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
NX3008PBKS v.	1 20110801	Product data sheet	-	-			

30 V, 200 mA dual P-channel Trench MOSFET

### 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### 30 V, 200 mA dual P-channel Trench MOSFET

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#### NX3008PBKS Product data sheet

#### 30 V, 200 mA dual P-channel Trench MOSFET

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